Supplementary information

ALD oxygen vacancy-rich amorphous Ga₂O₃ on three-dimensional urchin-like ZnO arrays for high-performance self-powered solar-blind photodetectors

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Fig. S1 SEM images of TiO₂/ZnO microsphere arrays.



Fig. S2 TEM mapping of (a) overlapped images, (b) Ga, (c) O, (d) Ti and (e) Zn. (f) spectra from element mapping.



Fig. S3 XRD spectra of V_0 -Ga₂O₃/ZnO and Ga₂O₃/ZnO.



Fig. S4 EIS curves of (a) $3D V_0$ -Ga₂O₃/ZnO with different thickness of Ga₂O₃ film under 254 nm illumination. EIS curves of $3D V_0$ -Ga₂O₃/ZnO with a Ga₂O₃ film thickness of (b) 4 nm, (c) 8 nm, (d) 12 nm under 254 nm illumination and dark environment.



Fig. S5 Durability test of 3D V_0 -Ga₂O₃/ZnO under continuous light radiation at 254 nm.



Fig. S6 SEM images of 3D $V_{\rm o}\text{-}Ga_2O_3/ZnO$ (a) before and (b) after the durability test.



Fig. S7 UPS curves of (a) ZnO and (b) Ga_2O_3 . Calculated band gaps of (c) ZnO and (d) Ga_2O_3 from transmittance.